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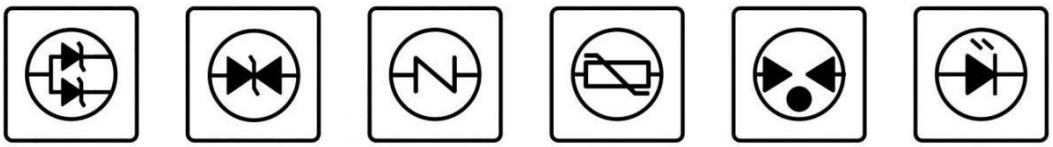


TPS763XXDBVR-MS

Product specification

GENERAL DESCRIPTION

The TPS763XXDBVR-MS series are a group of low-dropout (LDO) voltage regulators offering the benefits of wide input voltage range,low dropout voltage,low power consumption, and miniaturized packaging. Quiescent current of only 1.5μA makes these devices ideal for powering the battery-powered,always-on systems that require very little idle-state power dissipation to a longer service life.

The TPS763XXDBVR-MS series of linear regulators are stable with the ceramic output capacitor over its wide input range from 2V to 24V and the entire range of output load current (0mAto 300mA).

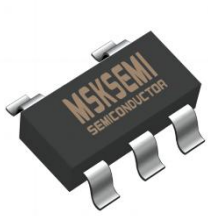
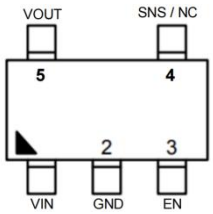
Features

- 1.5μA Ground Current at no Load
- ±2% Output Accuracy
- 300mA Output Current
- Wide Operating Input Voltage Range: 2V to 24V
- Dropout Voltage: 0.35V at 100mA / VOUT 5V
- Support Fixed Output Voltage 1.8V, 3.3V, 5V
- Stable with Ceramic or Tantalum Capacitor
- Current Limit Protection
- Over-Temperature Protection
- SOT-23-5 Packages Available

Applications

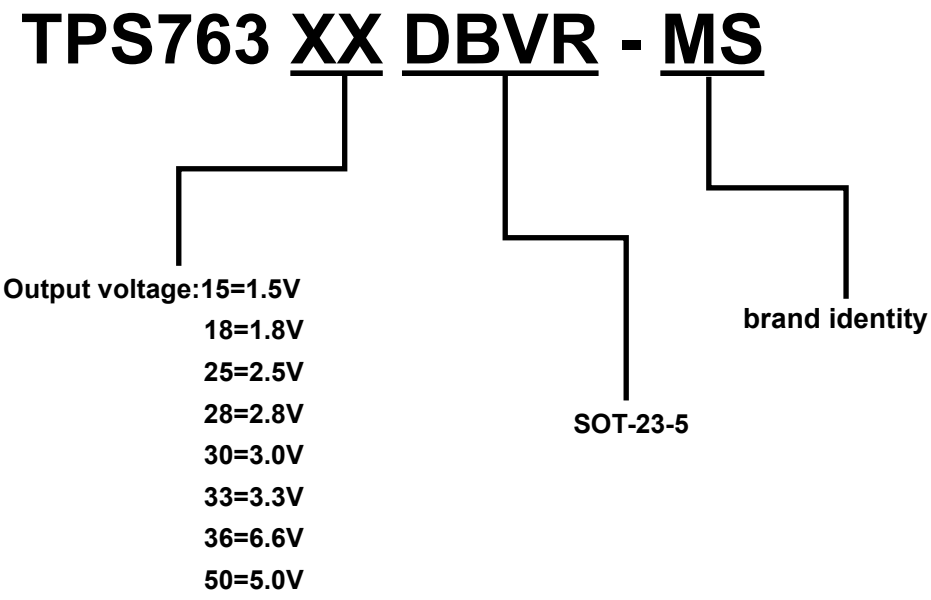
- Portable, Battery Powered Equipment
- Low Power Microcontrollers
- Laptop, Palmtops and PDAs
- Wireless Communication Equipment
- Audio/Video Equipment
- Car Navigation Systems
- Industrial Controls
- Weighting Scales
- Meters
- Home Automation

Reference News&Marking

SOT-23-5	Pin Configurations
	

TPS76315DBVR-MS	TPS76318DBVR-MS
	
TPS76325DBVR-MS	**TPS76328DBVR-MS**
	
TPS76330DBVR-MS	**TPS76333DBVR-MS**
	
TPS76336DBVR-MS	**TPS76350DBVR-MS**
	

Part Number Code



Description of Functional Pins

Pin No	Pin Name	Pin Function
2	GND	Ground
5	VOUT	Output of the Regulator
1	VIN	Input of Supply Voltage.
4	NC	No Internal Connection.
3	CE	Enable Control Input.

REEL SPECIFICATION

P/N	PKG	QTY
TPS763XXDBVR-MS	SOT-23-5	3000

Typical Application Circuits

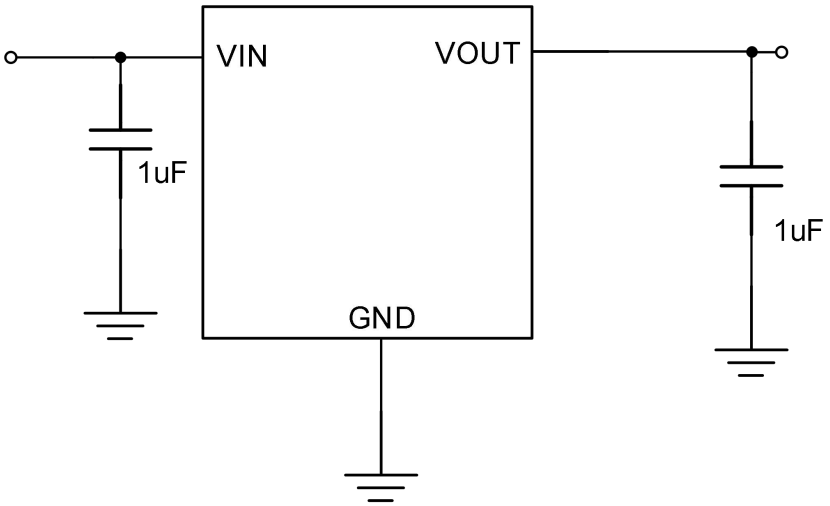
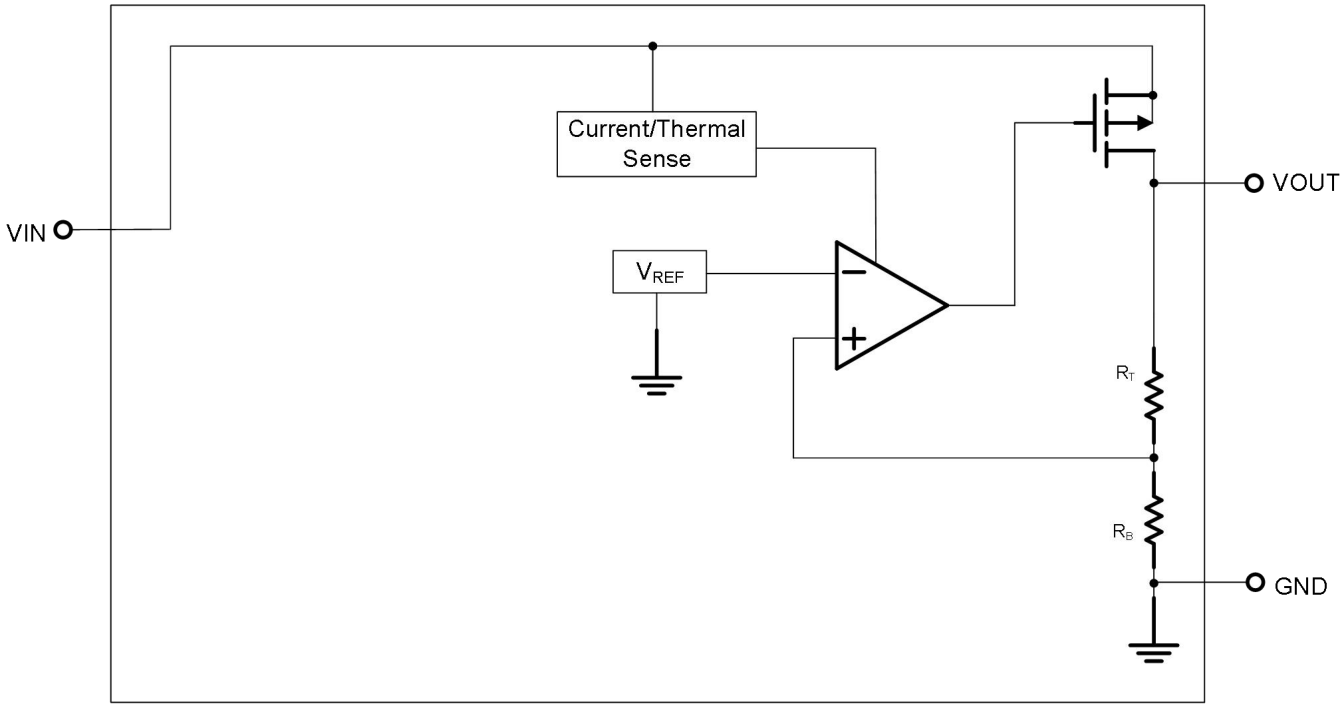


Figure 1: Application circuit of Fixed V_{OUT} LDO

Function Block Diagram



Absolute Maximum Ratings (Note 1)

VIN to GND ---------- 0.3V to 28V

VOUT to GND

1.8V,3.3V,5V---------- 0.3V to 6.0V

VOUT to VIN ---------- 28V to 0.3V

Package Thermal Resistance (Note 2)

θJA ---------- 200 °C /W

Lead Temperature (Soldering, 10 sec.) ---------- 260 ℃

Junction Temperature ---------- 150 ℃

Storage Temperature Range ---------- 40 °C to 150 ℃

ESD Susceptibility

HBM ---------- 2KV

MM ---------- 200V

Recommended Operating Conditions

Input Voltage VIN ---------- 2.0V to 24V

Junction Temperature Range---------- -40℃ to 125℃

AmbientTemperatureRange---------- -40℃ to 85℃

Electrical Characteristics

(V_{IN} =15V, V_{EN} =5V, T_A=25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Supply Voltage	V_{IN}		2	--	24	V
DC Output Voltage Accuracy		I_{LOAD} =0.1mA	-2		2	%
Dropout Voltage (I_{LOAD} =100mA)	V_{DROP}	V_{OUT} ≥ 5V	--	0.35		V
	$V_{DROP\_3.3V}$	V_{OUT} = 3.3V		0.42		
	$V_{DROP\_1.8V}$	V_{OUT} = 1.8V		0.5		
Ground Current (I_{LOAD} = 0mA)	I_Q	V_{OUT} = 5V		2.2		μA
Line Regulation	ΔLINE	I_{LOAD} =1mA, 5 ≤ V_{IN} ≤ 30V	--	0.3		%
Load Regulation	ΔLOAD	1mA≤ I_{LOAD} ≤ 0.2A		0.1		%
Output Current Limit	I_{LIM}	V_{OUT} =0		300		mA
Power Supply Rejection Ratio	PSRR	V_{OUT} =5V, I_{LOAD} =1mA, V_{IN} = 12V, f = 100Hz		70		dB
Thermal Shutdown Temperature	T_{SD}	I_{LOAD} =10mA	--	160	--	°C
Thermal Shutdown Hysteresis	ΔT_{SD}			15		°C

Note 1. Stresses beyond those listed “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions may affect device reliability.

Application Guideline

Input and Output Capacitor Requirements

The external input and output capacitors of TPS763XXDBVR-MS series must be properly selected for stability and performance. Use a 1μF or larger input capacitor and place it close to the IC's VIN and GND pins. Any output capacitor meeting the minimum 1mΩ ESR (Equivalent Series Resistance) and effective capacitance between 1μF and 22μF requirement may be used. Place the output capacitor close to the IC's VOUT and GND pins. Increasing capacitance and decreasing ESR can improve the circuit's PSRR and line transient response.

Current Limit

The TPS763XXDBVR-MS series contain the current limiter of output power transistor, which monitors and controls the transistor, limiting the output current to 500mA (typical).

The output can be shorted to ground indefinitely without damaging the part.

Dropout Voltage

The TPS763XXDBVR-MS series use a PMOS pass transistor to achieve low dropout. When (VIN – VOUT) is less than the dropout voltage (V_{DROP}), the PMOS pass device is in the linear region of operation and the input-to-output resistance is the $RDS_{(ON)}$ of the PMOS pass element. V_{DROP} scales approximately with the output current because the PMOS device behaves as a resistor in dropout condition.

As any linear regulator, PSRR and transient response are degraded as (VIN – VOUT) approaches dropout condition.

OTP (Over Temperature Protection)

The over temperature protection function of TPS763XXDBVR-MS series will turn off the P-MOSFET when the junction temperature exceeds 160°C (typ.). Once the junction temperature cools down by approximately 15°C, the regulator will automatically resume operation.

Thermal Application

For continuous operation, do not exceed the absolute maximum junction temperature. The maximum power dissipation depends on the thermal resistance of the IC package, PCB layout, rate of surrounding airflow, and difference between junction and ambient temperature. The maximum power dissipation can be calculated as below:

The max PD (Max)= (125°C − 25°C) / (200°C/W) = 0.5W .

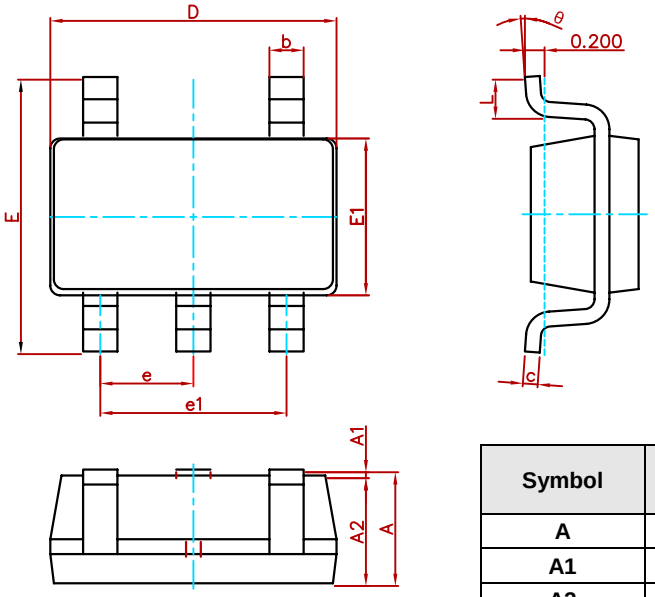
Power dissipation (PD) is equal to the product of the output current and the voltage drop across the output pass element, as shown in the equation below:

PD = (VIN – VOUT) × IOUT

Layout Consideration

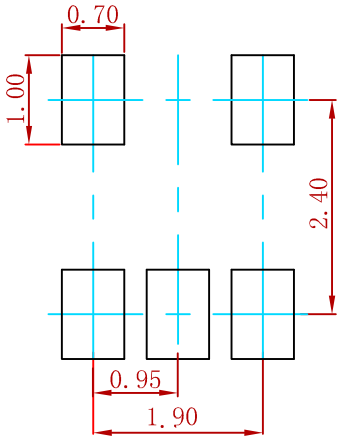
By placing input and output capacitors on the same side of the PCB as the LDO, and placing them as close as is practical to the package can achieve the best performance. The ground connections for input and output capacitors must be back to the TPS763XXDBVR-MS ground pin using as wide and as short of a copper trace as is practical. Connections using long trace lengths, narrow trace widths, and/or connections through via must be avoided. These add parasitic inductances and resistance that results in worse performance especially during transient conditions.

Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	2.650	2.950	0.104	0.116
E1	1.500	1.700	0.059	0.067
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.05mm.
3.The pad layout is for reference purposes only.

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